



FIG. 1
PRIOR ART

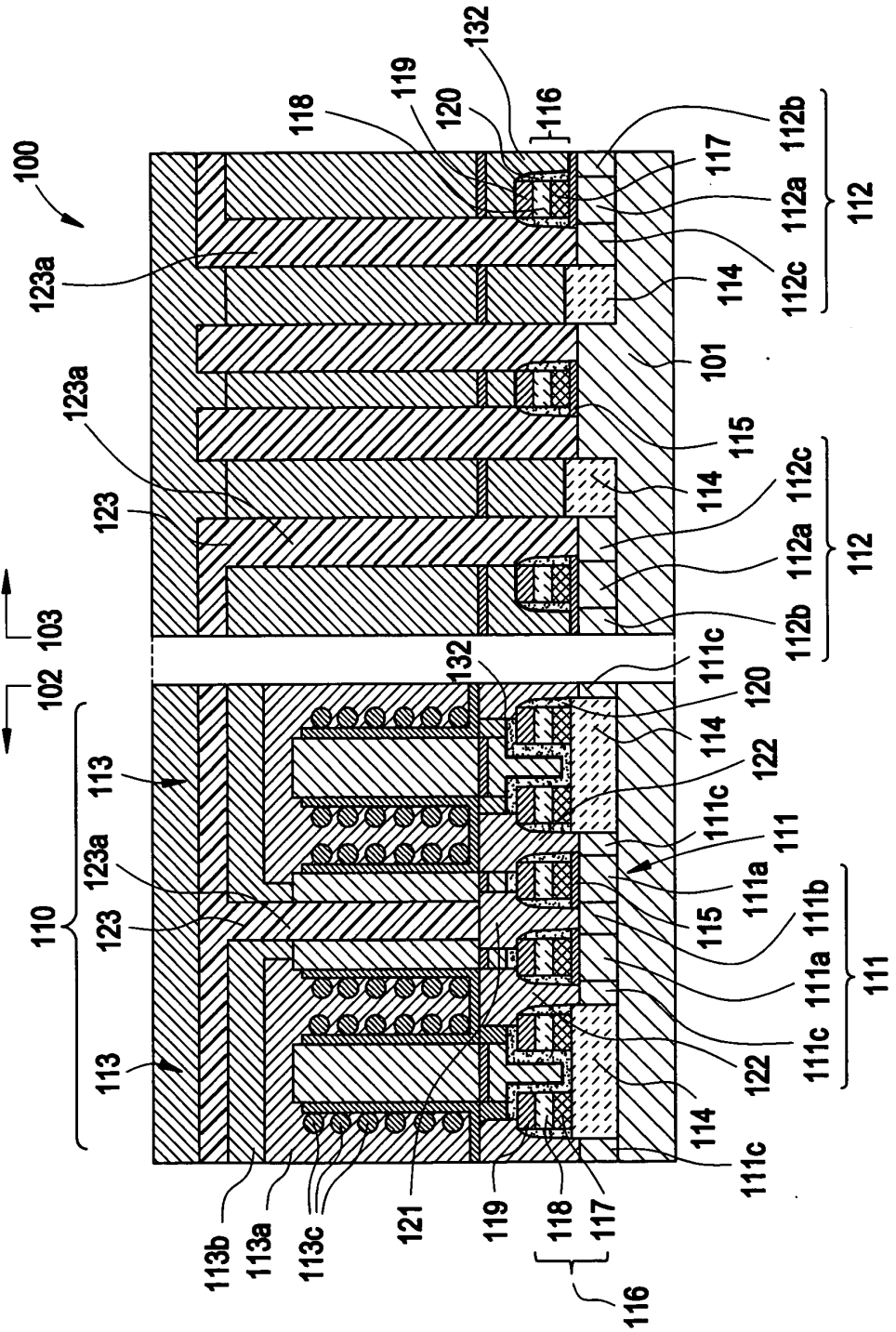
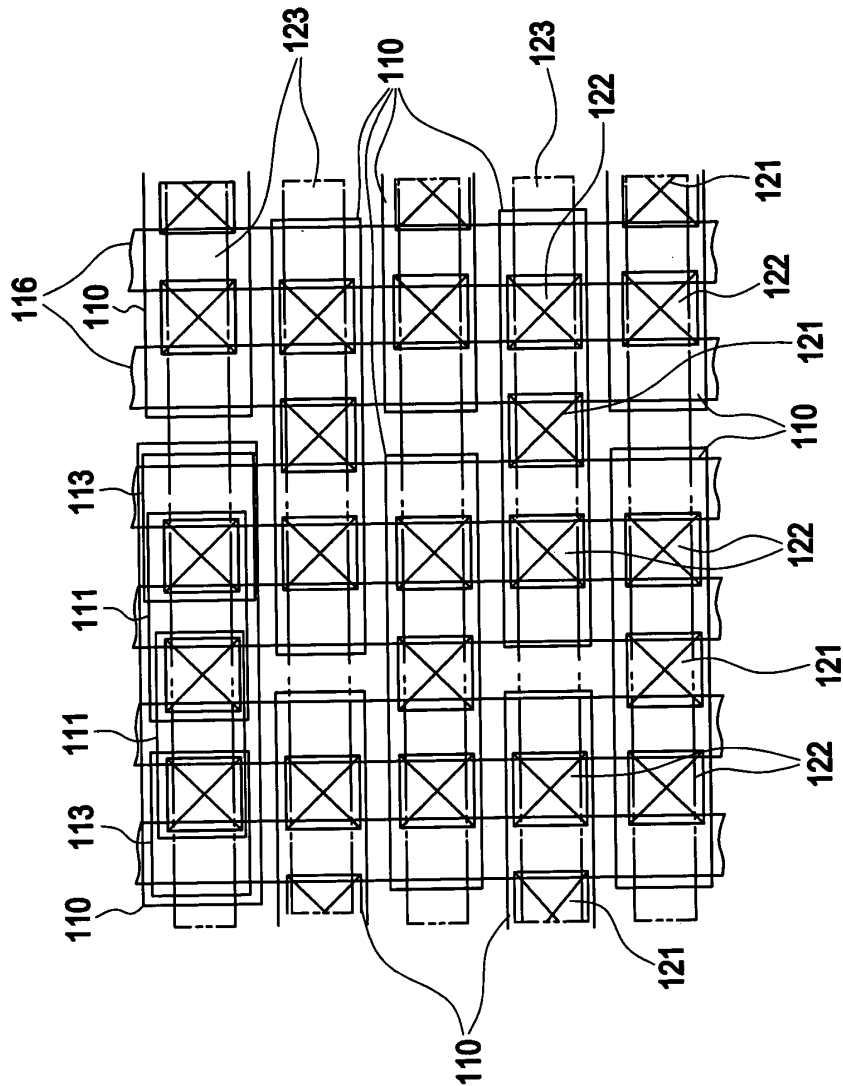




FIG. 2
PRIOR ART





SEMICONDUCTOR DEVICE UTILIZING HIGH-DENSITY AND LOW-DENSITY REGIONS OF TRANSISTOR ELEMENTS ON SINGLE SEMICONDUCTOR SUBSTRATE, AND METHOD OF MANUFACTURING SUCH SEMICONDUCTOR DEVICE
 Inventor(s): Toshiyuki HIROTA, et al.
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FIG. 3
PRIOR ART

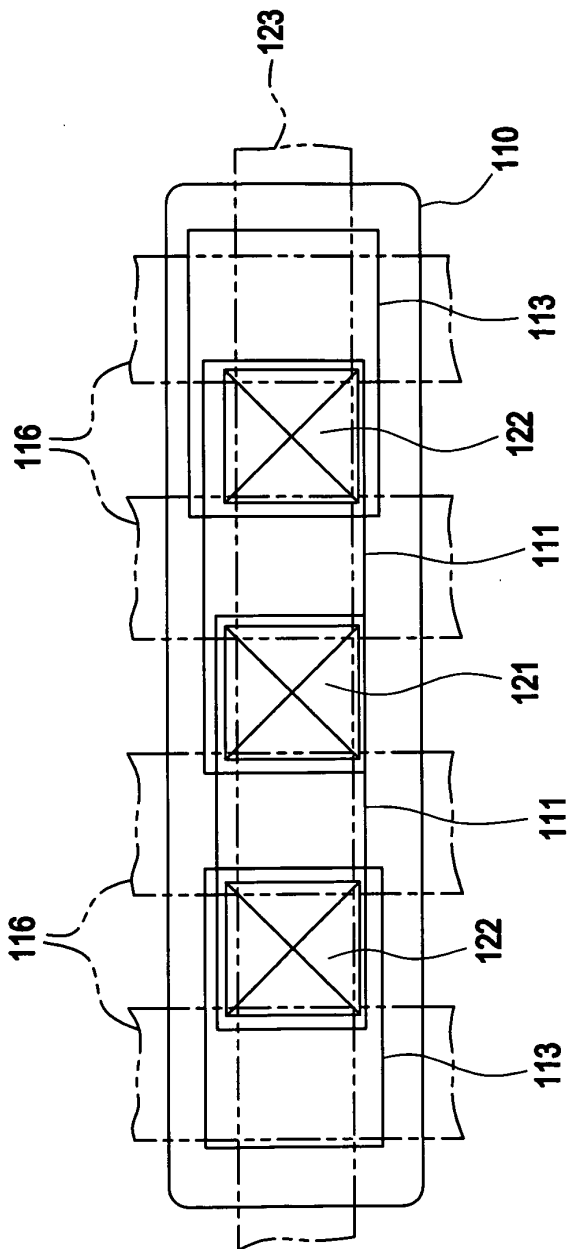
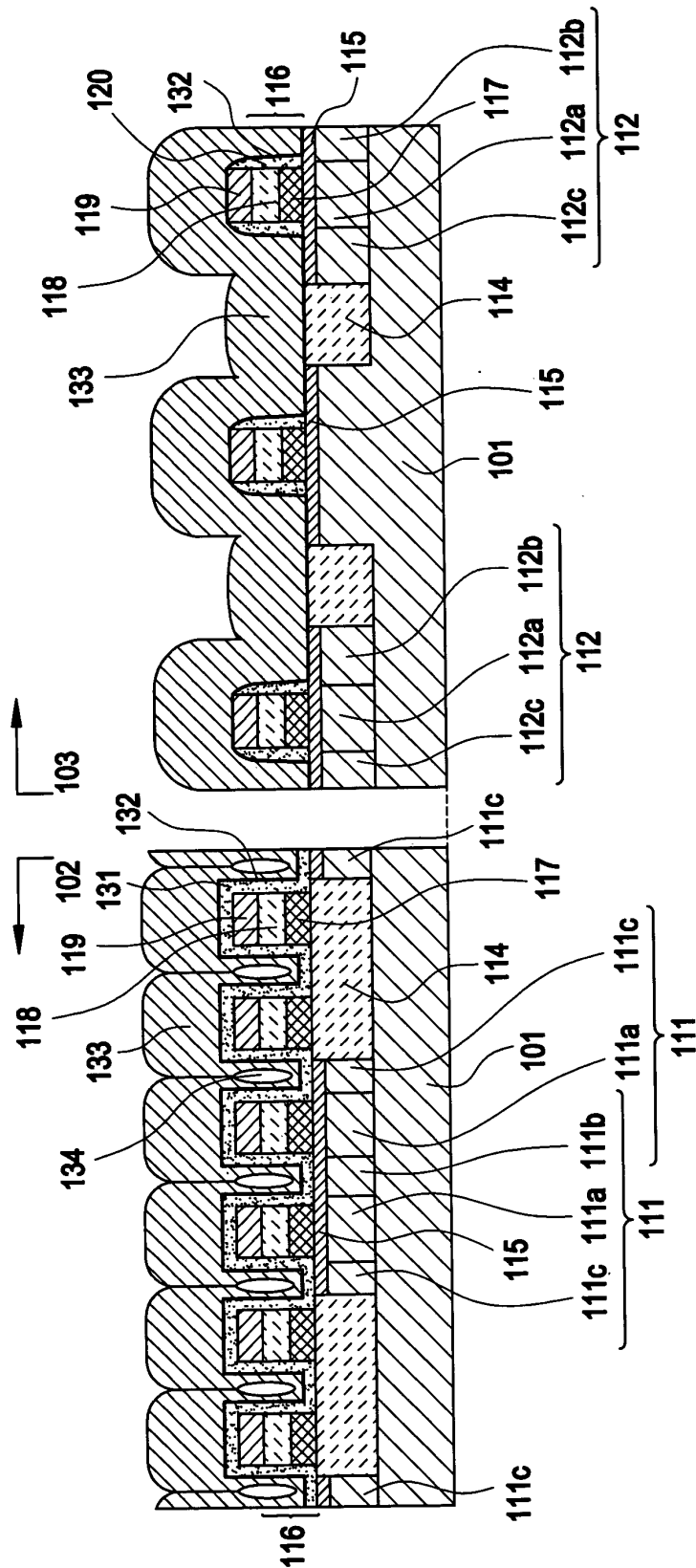




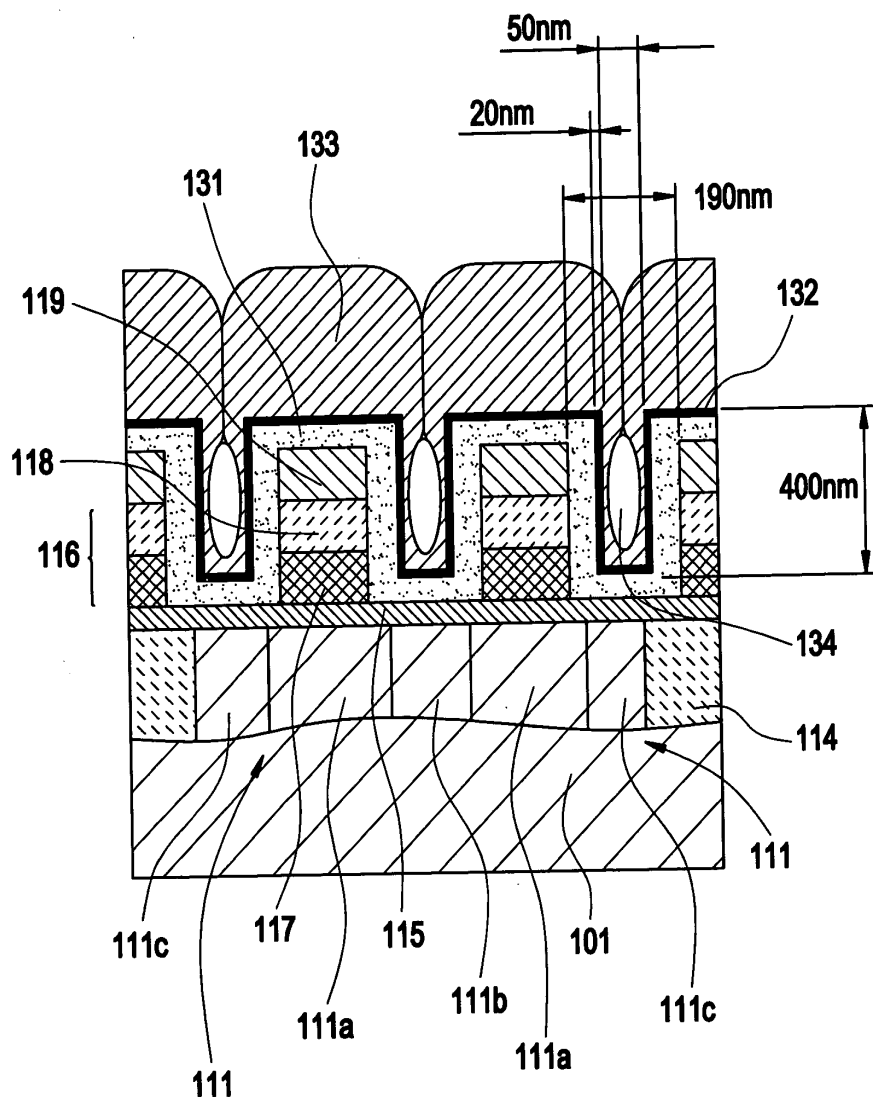
FIG. 4
PRIOR ART





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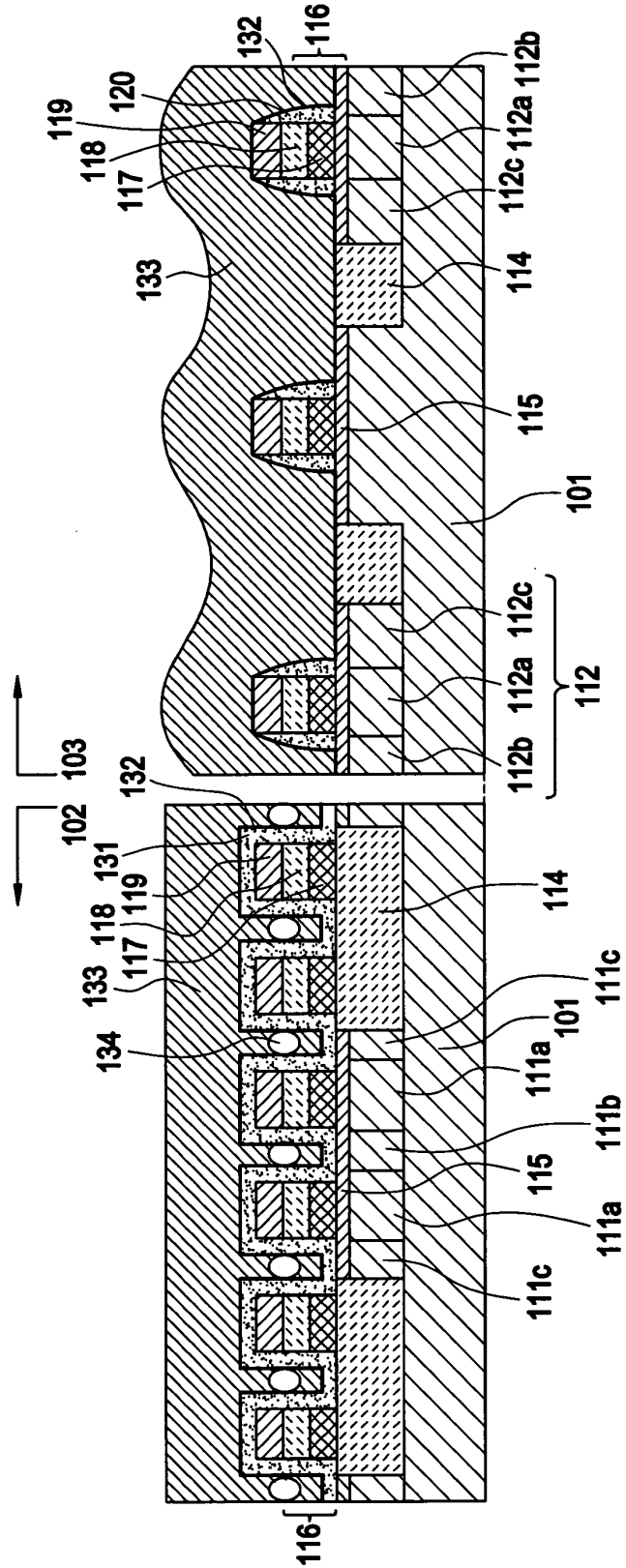
FIG. 5
PRIOR ART





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FIG. 6
 PRIOR ART





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FIG. 7
PRIOR ART

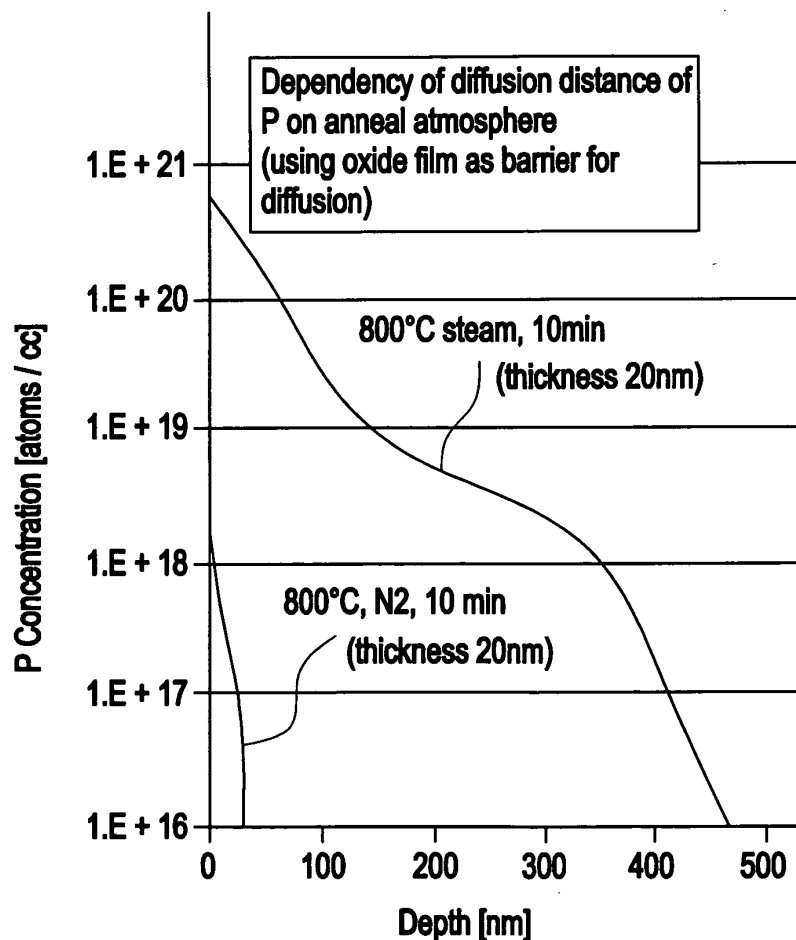
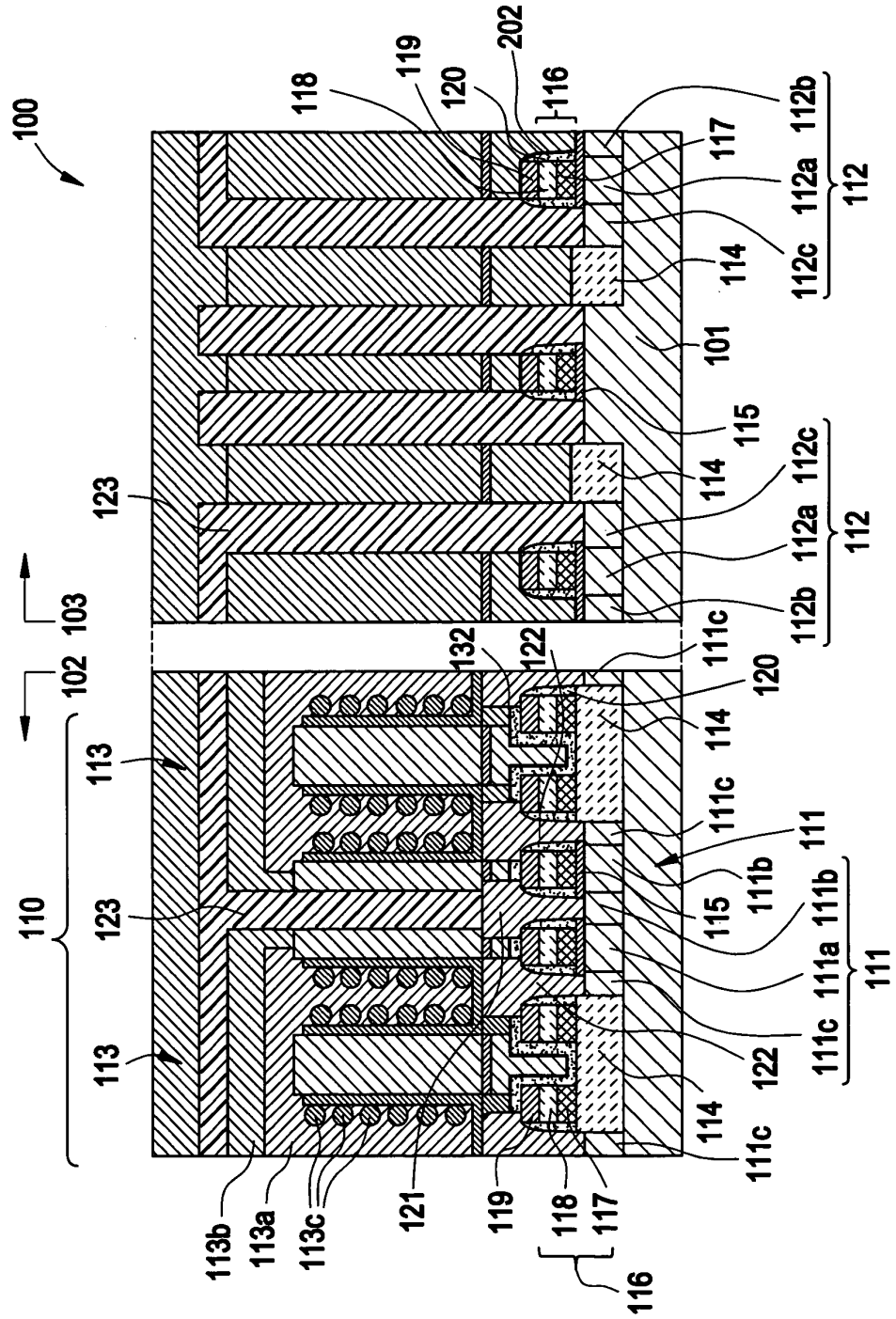




FIG. 8





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FIG. 9A

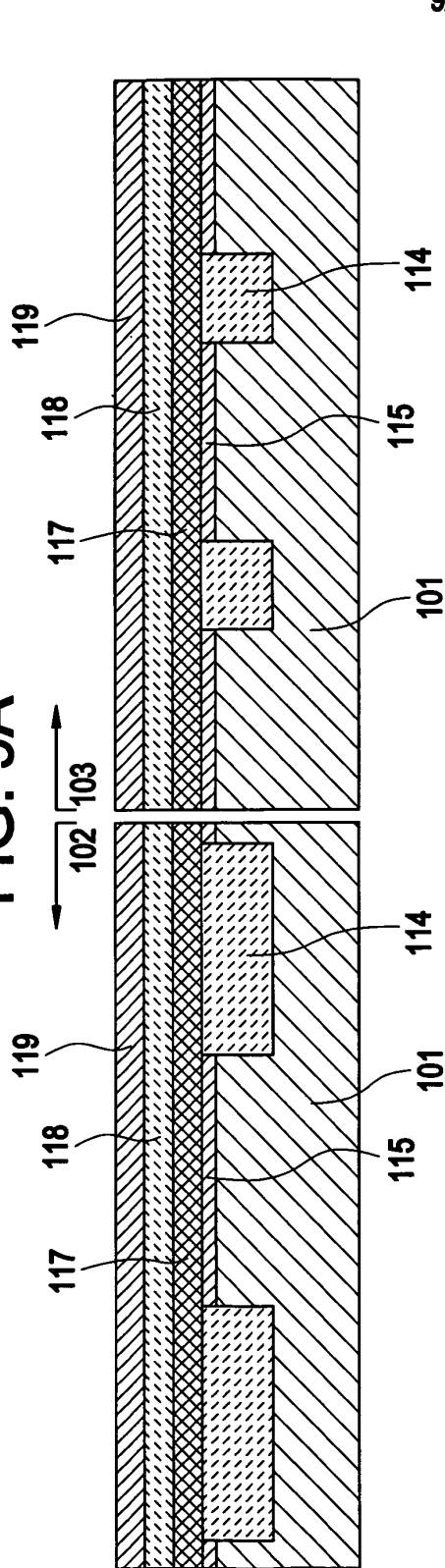
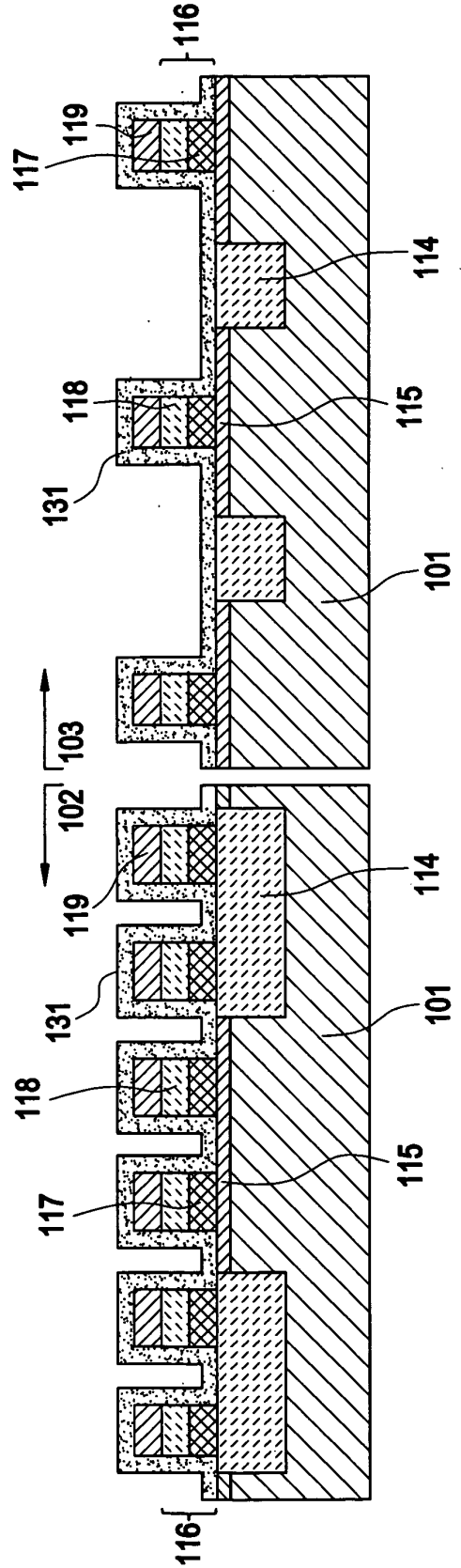
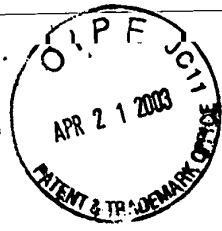


FIG. 9B





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FIG. 10A

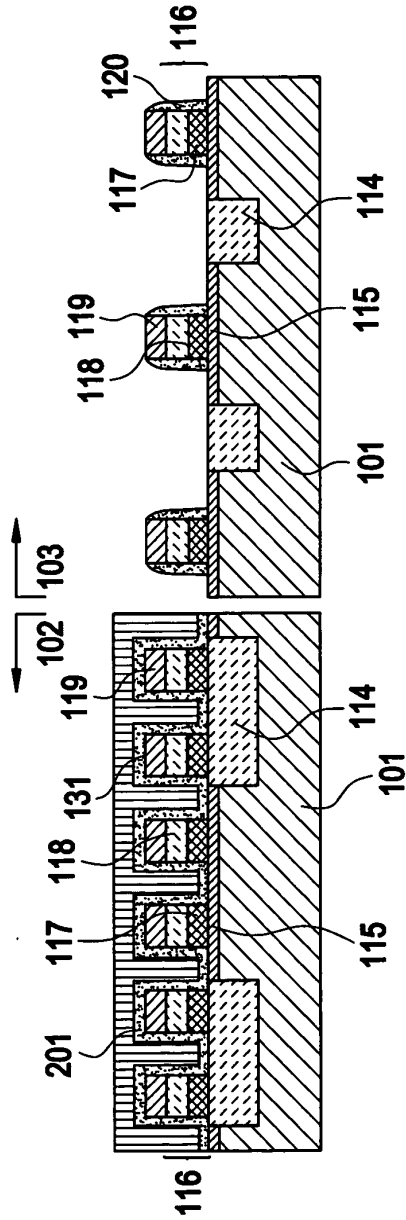
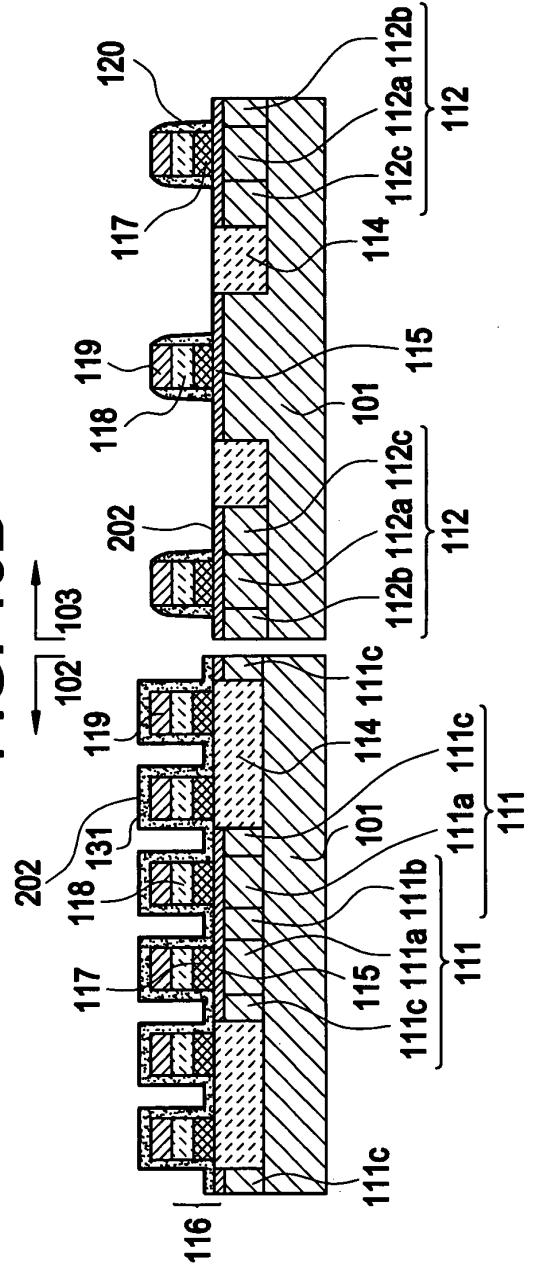
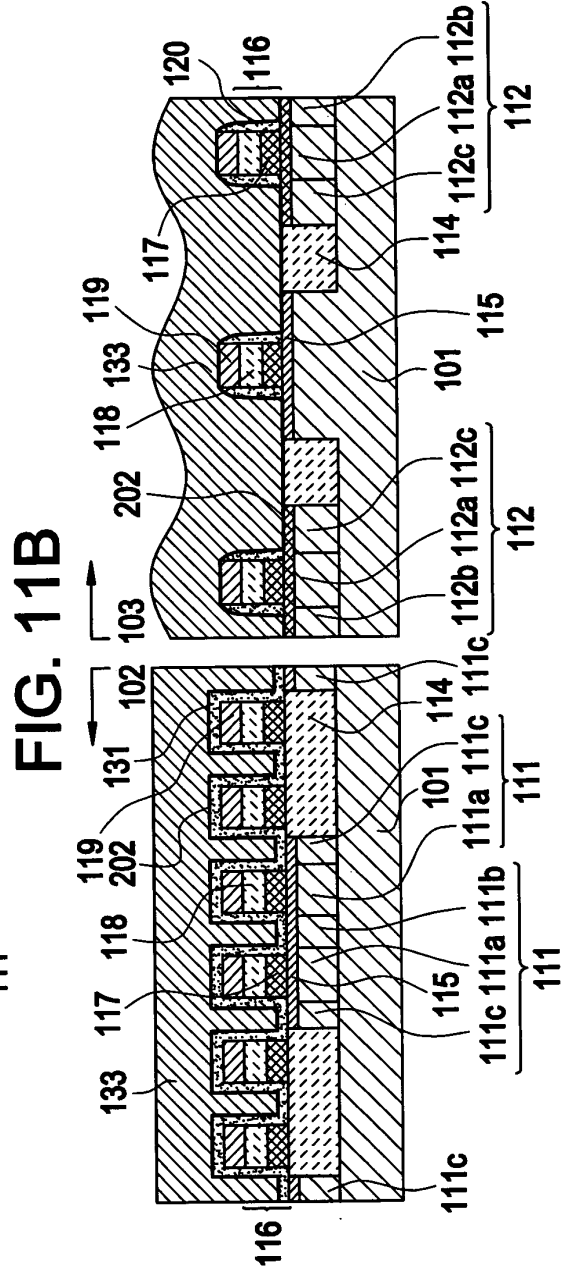
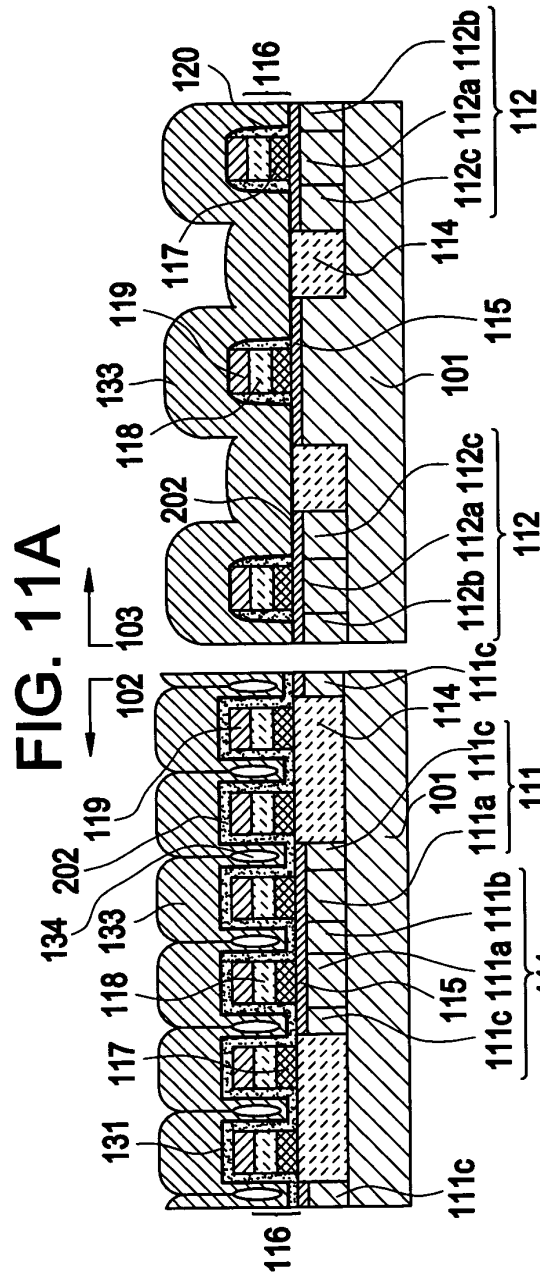


FIG. 10B







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FIG. 12A

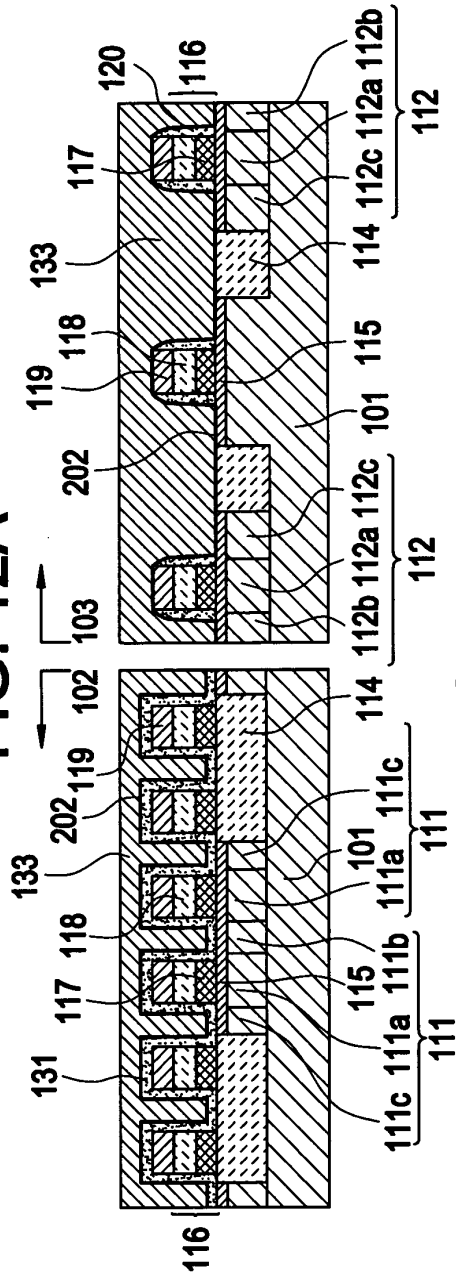


FIG. 12B

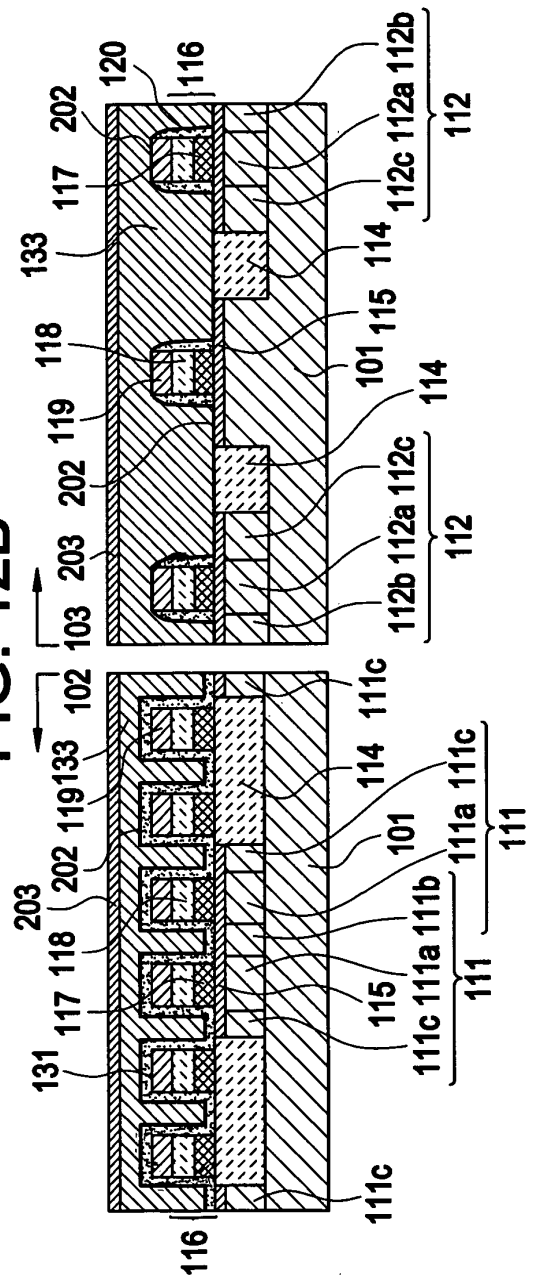


FIG. 13A

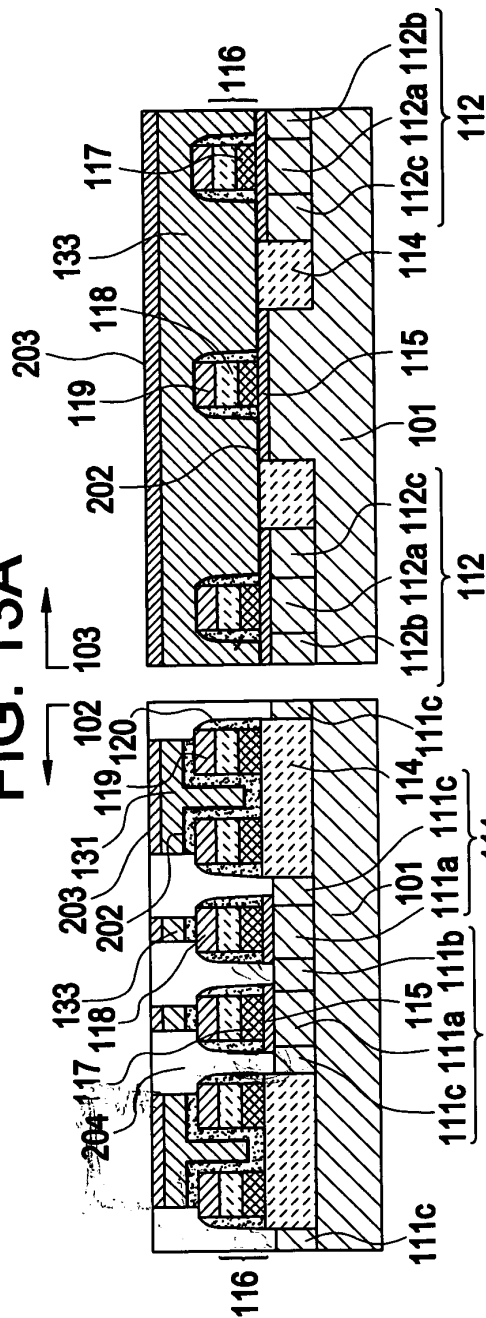
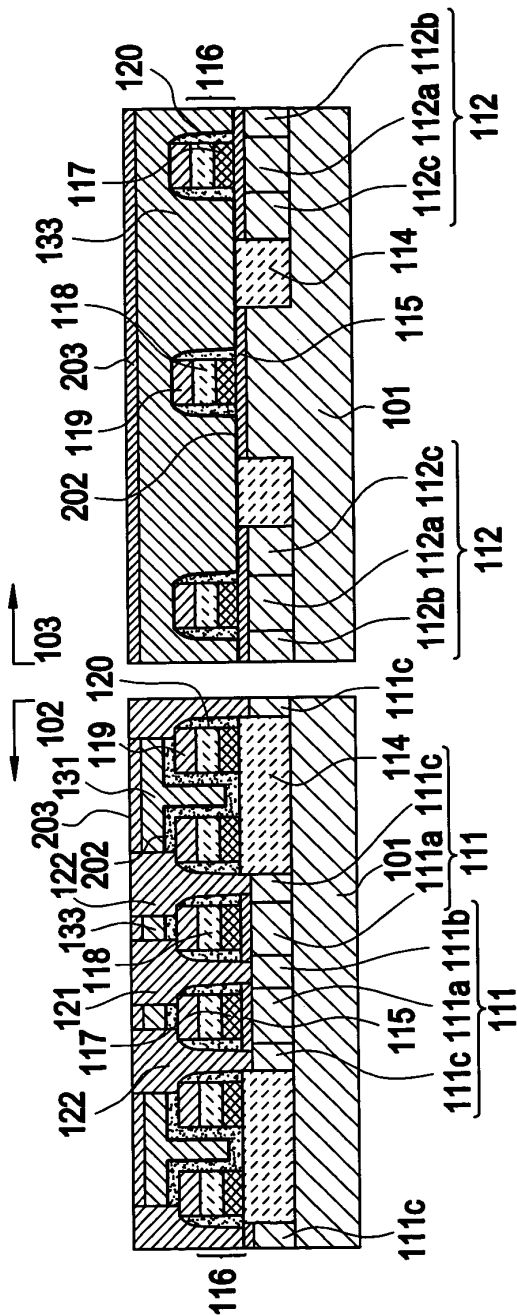
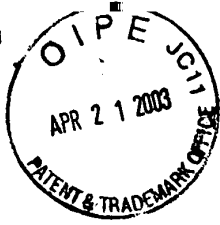


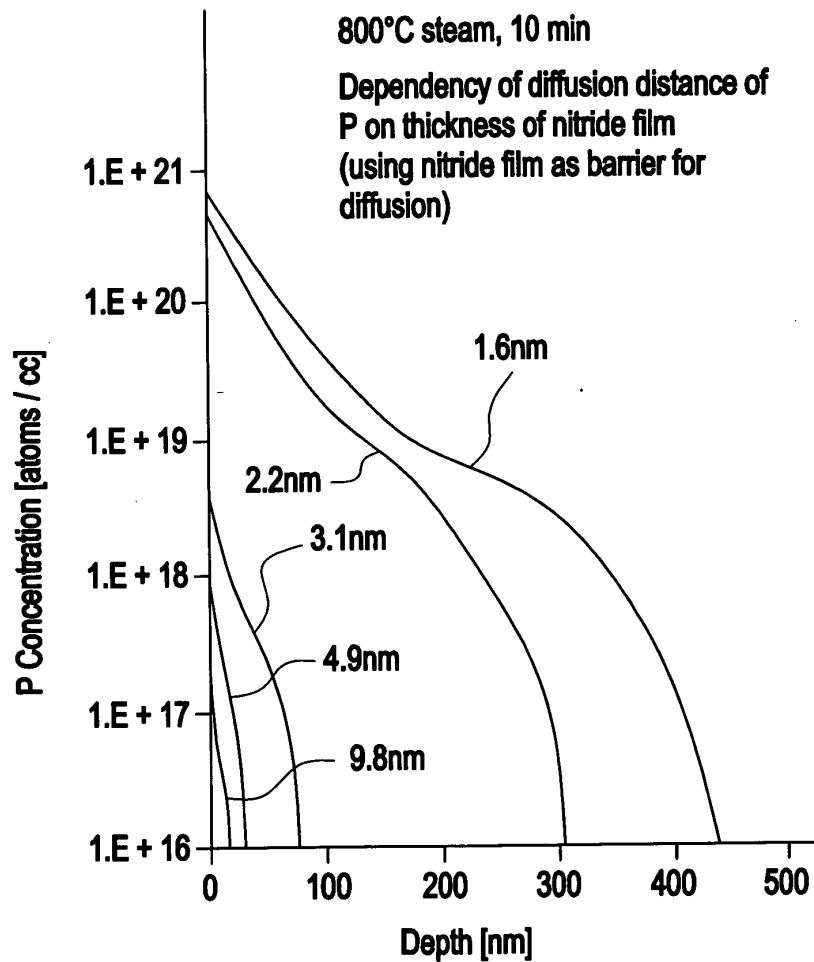
FIG. 13B





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FIG. 14





Title: SEMICONDUCTOR DEVICE WITH LOW-DENSITY REGIONS OF TRANSISTOR ELEMENTS ON SINGLE SEMICONDUCTOR SUBSTRATE, AND METHOD OF MANUFACTURING SUCH SEMICONDUCTOR DEVICE
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FIG. 15

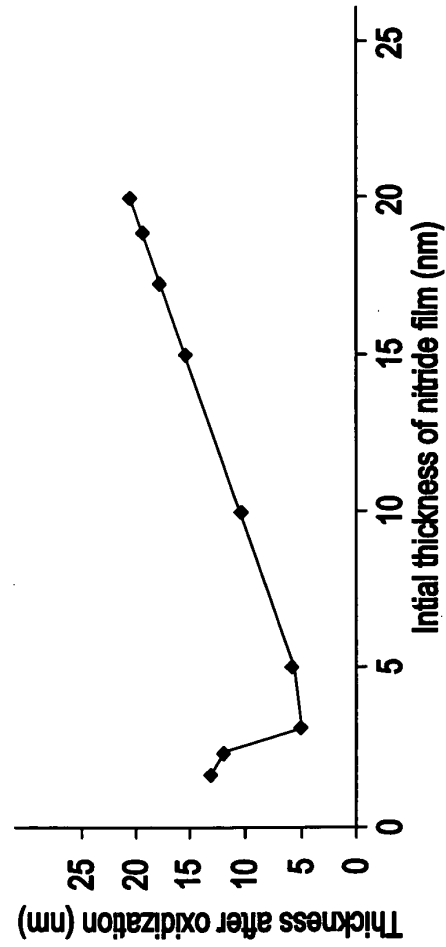




FIG. SEMICONDUCTOR DEVICE HAVING LOW-DENSITY REGIONS OF TRANSISTOR ELEMENTS ON SINGLE SEMICONDUCTOR SUBSTRATE, AND METHOD OF MANUFACTURING SUCH SEMICONDUCTOR DEVICE

Inventor(s): Toshiyuki HIROTA, et al.

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FIG. 16

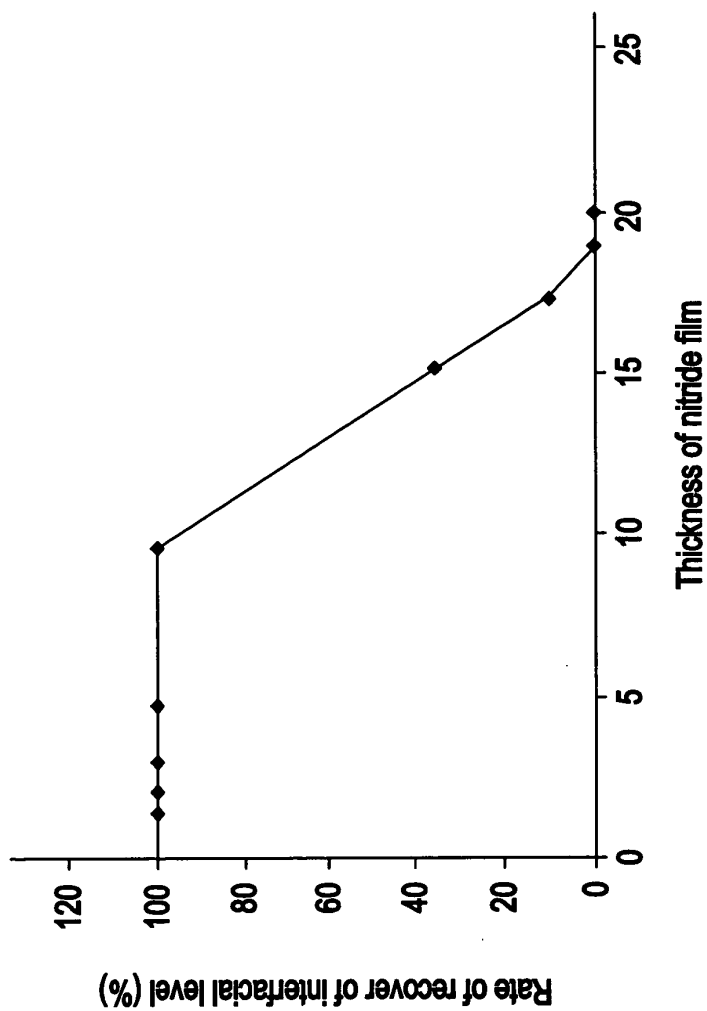
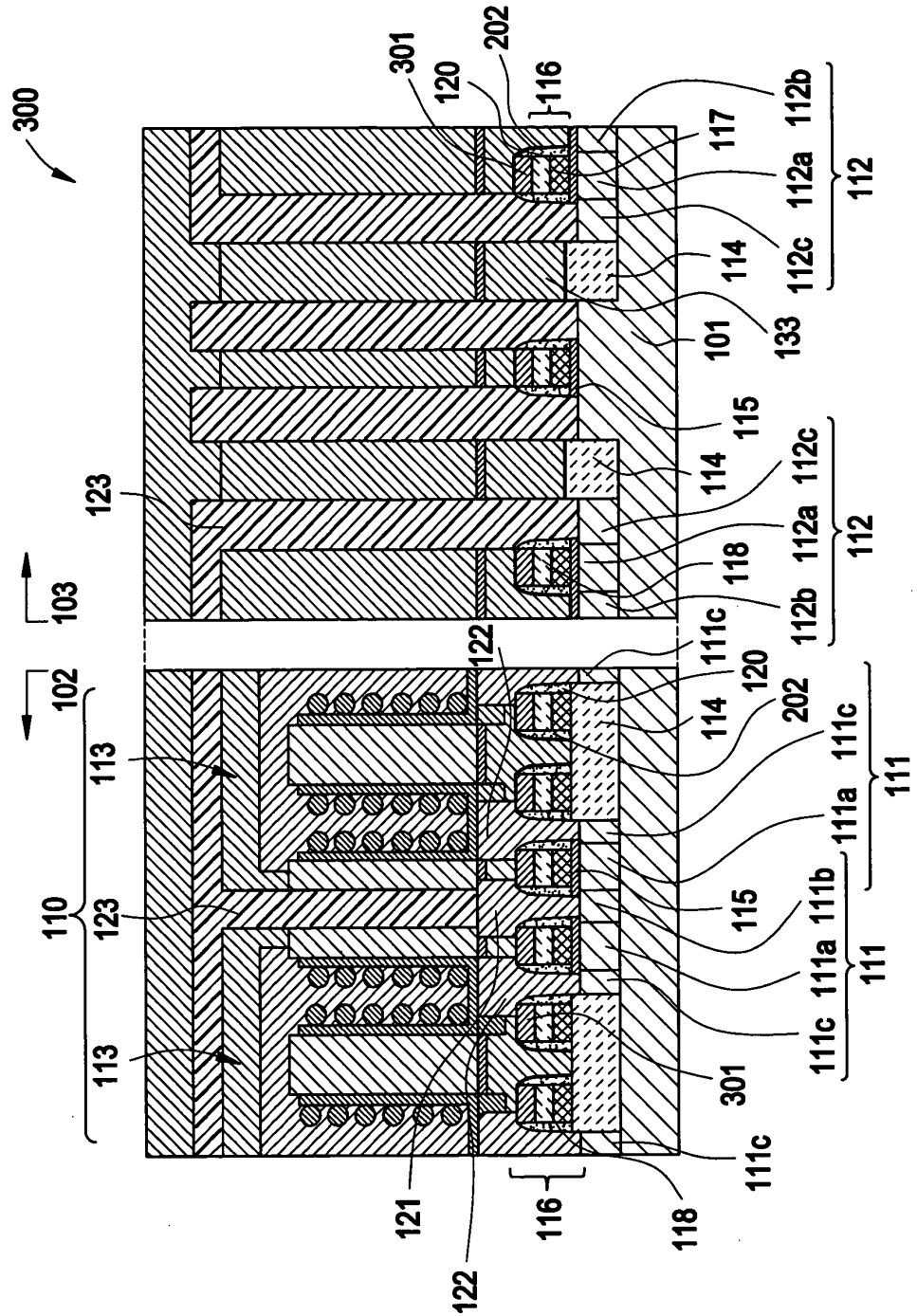




FIG. 17





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FIG. 18A

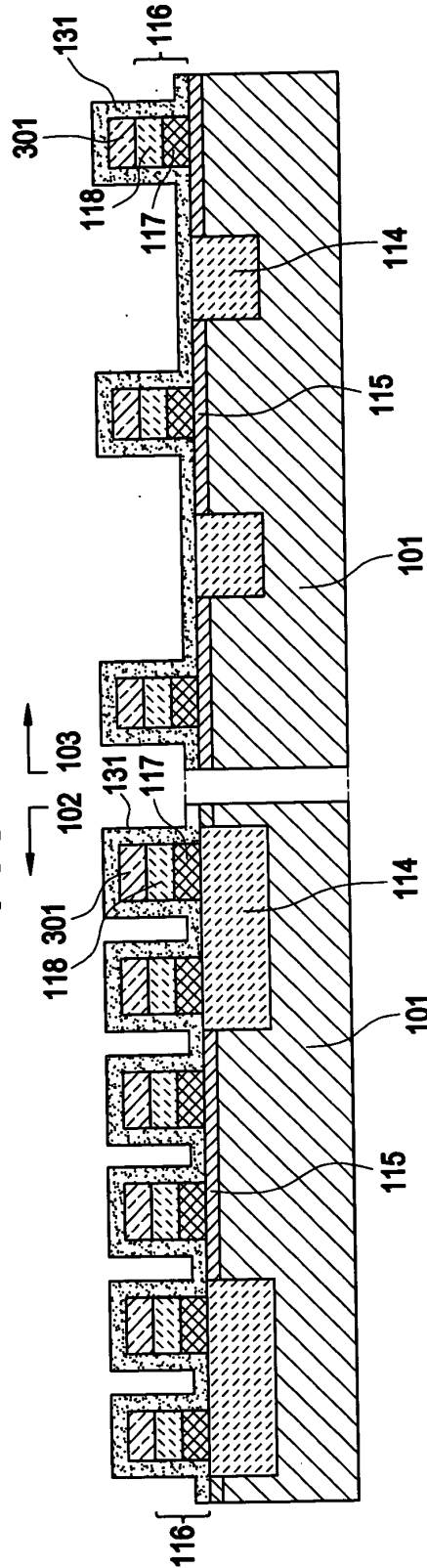
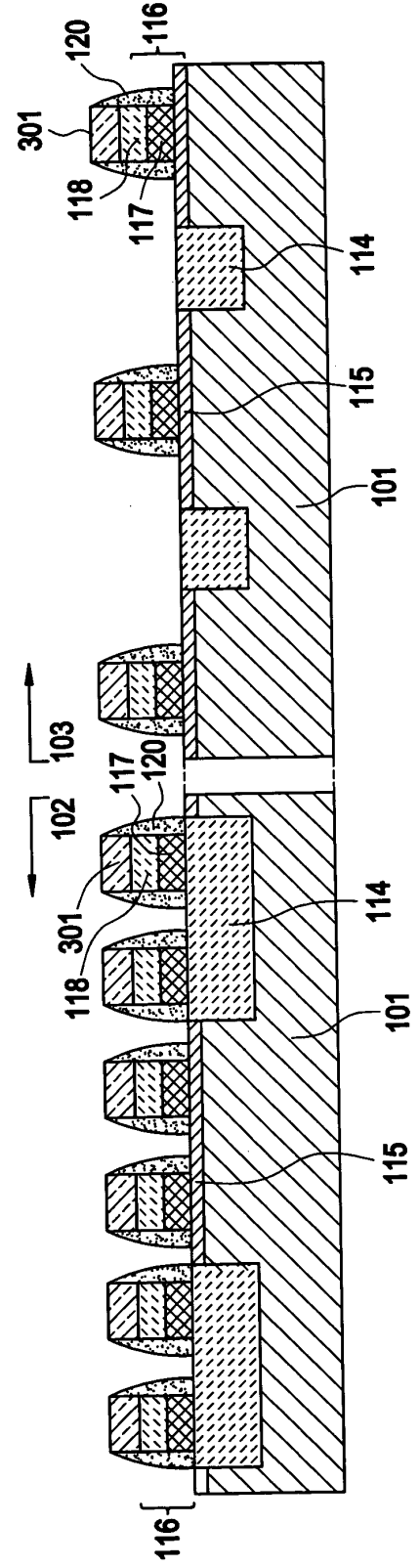


FIG. 18B





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FIG. 19A

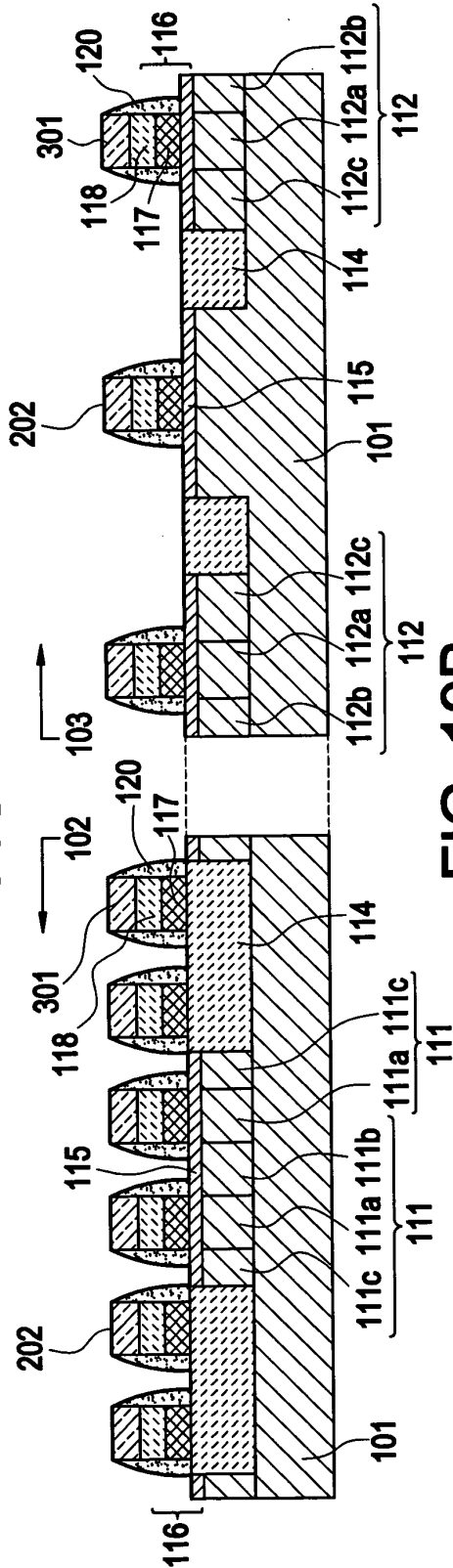
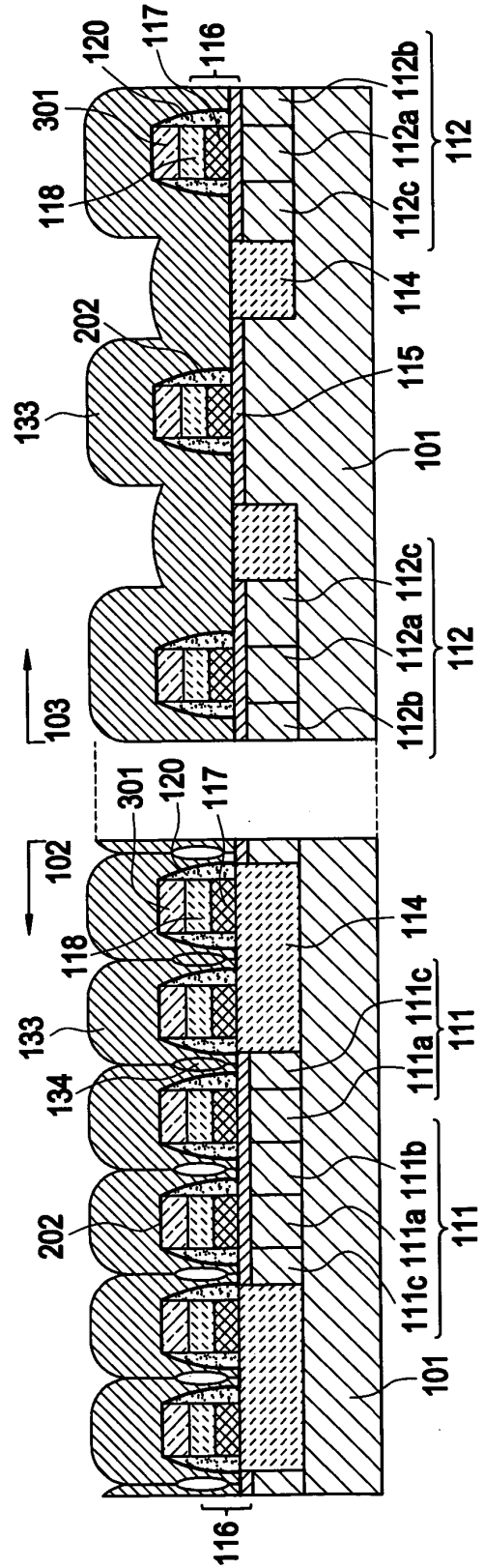


FIG. 19B





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FIG. 20A

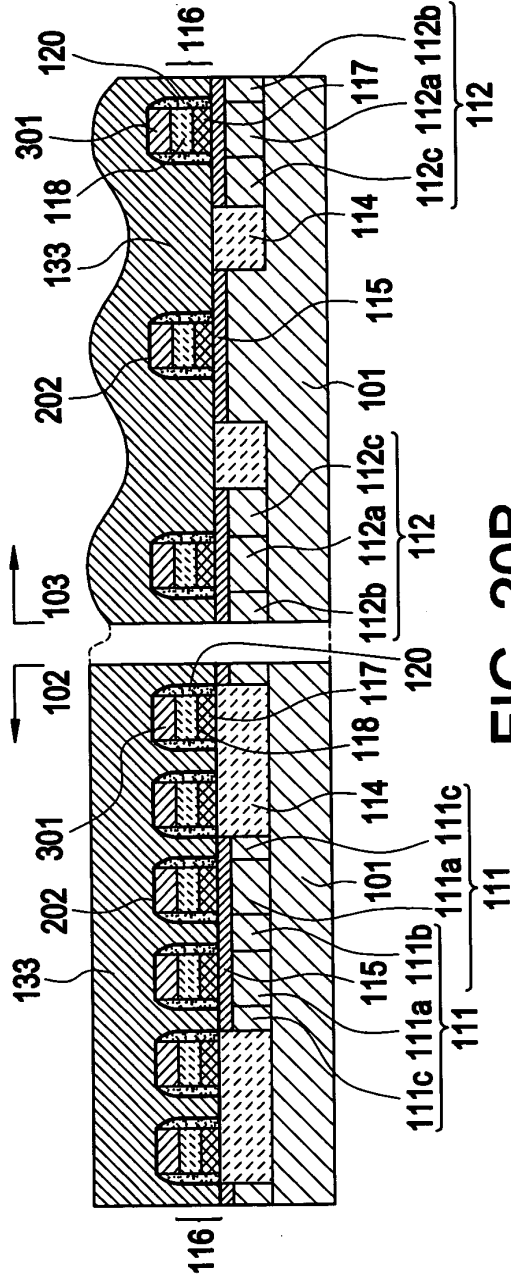


FIG. 20B

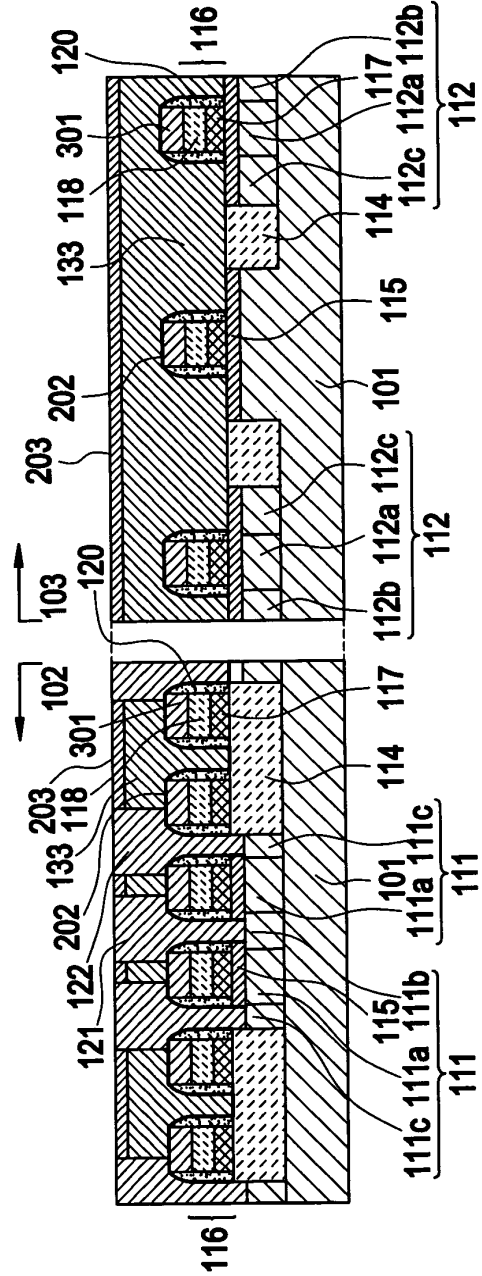
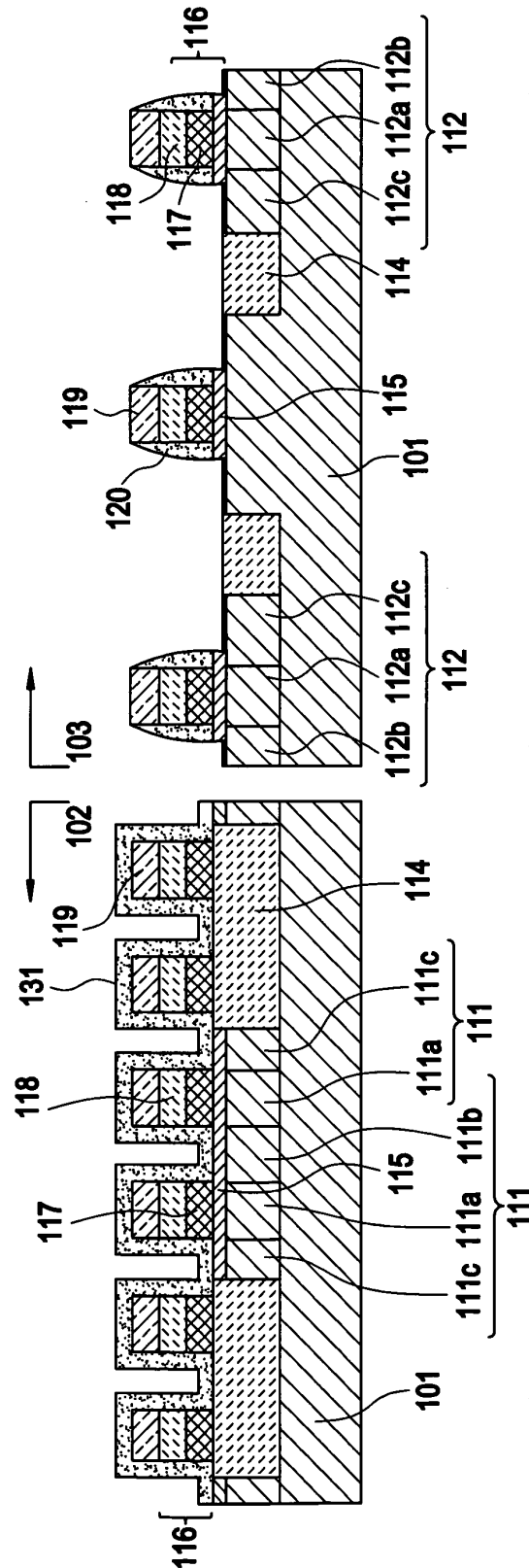




FIG. 21

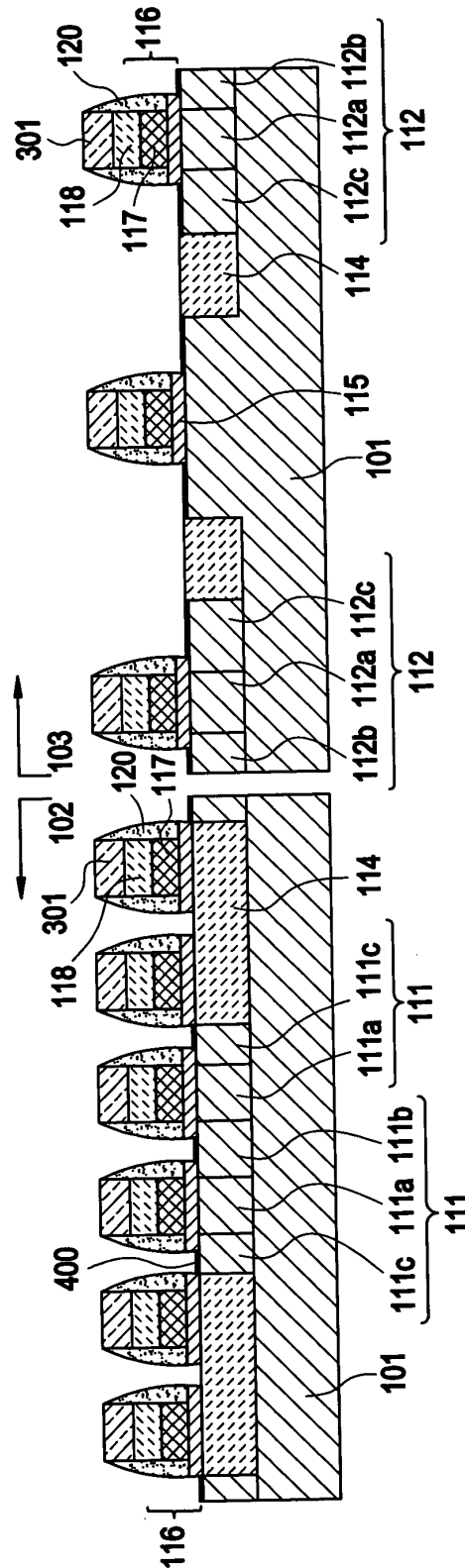




Title: SEMICONDUCTOR DEVICE WITH HIGH- AND LOW-DENSITY REGIONS OF TRANSISTOR ELEMENTS ON SINGLE SEMICONDUCTOR SUBSTRATE, AND METHOD OF MANUFACTURING SUCH SEMICONDUCTOR DEVICE
 Inventor(s): Toshiyuki HIROTA, et al.
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FIG. 22





Title: SEMICONDUCTOR DEVICE WITH HIGH- AND LOW-DENSITY REGIONS OF TRANSISTOR ELEMENTS ON SINGLE SEMICONDUCTOR SUBSTRATE, AND METHOD OF MANUFACTURING SUCH SEMICONDUCTOR DEVICE
 Inventor(s): Toshiyuki HIROTA, et al.
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FIG. 23

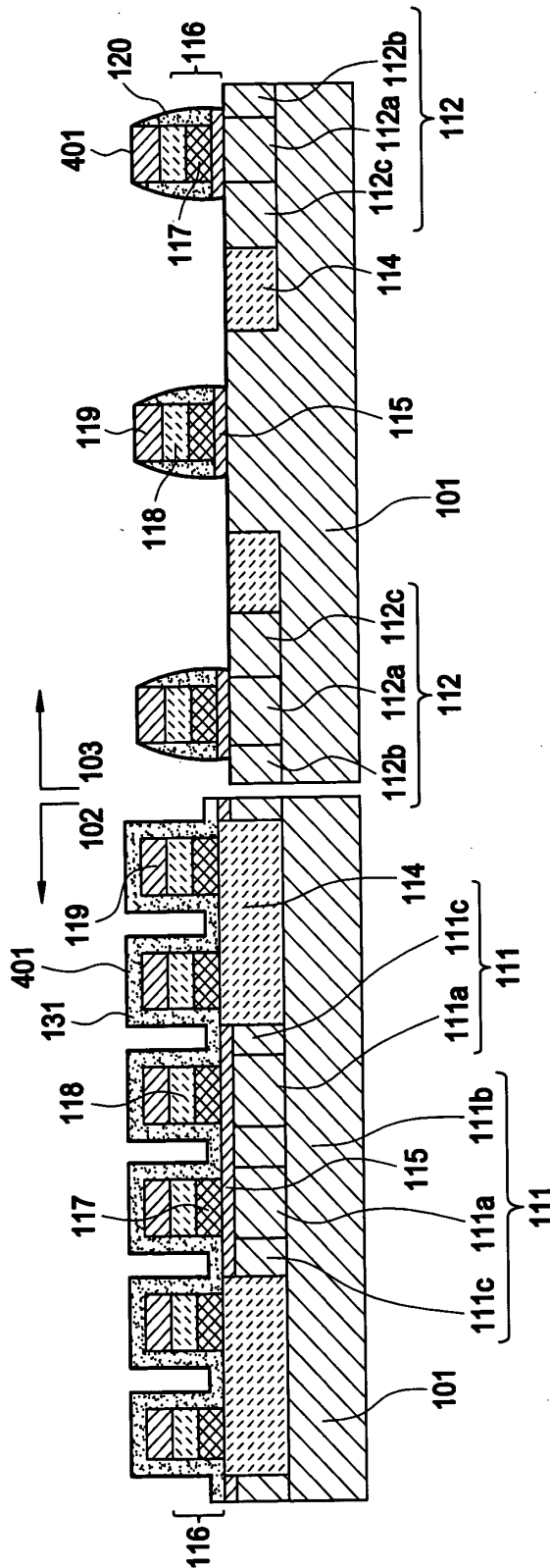




FIG. 24

